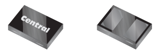
CTLTVS6V2

SURFACE MOUNT SILICON TRANSIENT VOLTAGE SUPPRESSOR

TLP Tiny Leadless Package™

Specified by BREAKDOWN VOLTAGE


Top View Bottom View

TLM2D3D6 CASE

Central™ Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CTLTVS6V2 is a low leakage, fast response silicon TVS packaged in an ultra small, ultra low profile TLM2D3D6 surface mount case. This device is designed to protect sensitive equipment against ESD damage.

MARKING CODE: S

APPLICATIONS:

- User interface protection
- Voltage rail protection
- Data line protection
- Voltage clamping

FEATURES:

- Ultra small, ultra low profile 0.3mm x 0.6mm x 0.3mm TLP™ leadless surface mount package
- High peak pulse current capability
- Low leakage current
- 15kV ESD protection

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Peak Power Dissipation (8x20μs)	P_{PK}	35	W
ESD Voltage (IEC 61000-4-2, Air)	V_{ESD}	15	kV
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C) V_F=1.0V MAX @ I_F=10mA

Maximum Reverse Stand-off Voltage V_{RWM}	Breakdown Voltage V_{BR} @ I_T			Test Current I_T	Maximum Reverse Leakage Current I_R @ V_{RWM}	Maximum Clamping Voltage V_C @ I_{PP}	Peak Pulse Current I_{PP}	Typical Junction Capacitance @ 0V Bias C_J
V	MIN V	NOM V	MAX V	mA	μA	V	A	pF
4.0	5.8	6.2	6.6	5.0	1.0	10.7	3.0	25

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TRANSIENT VOLTAGE SUPPRESSOR

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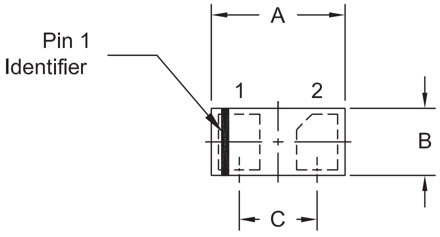
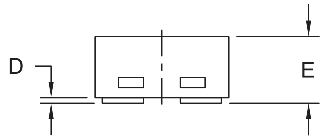
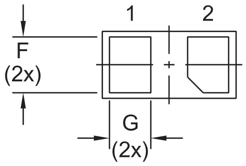
TLM2D3D6 CASE - MECHANICAL OUTLINE



TOP VIEW



SIDE VIEW



BOTTOM VIEW R2

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.022	0.026	0.55	0.65
B	0.010	0.014	0.25	0.35
C	0.014		0.35	
D	0.000	0.002	0.00	0.05
E	0.011	0.013	0.28	0.32
F	0.008	0.012	0.20	0.30
G	0.005	0.009	0.13	0.24

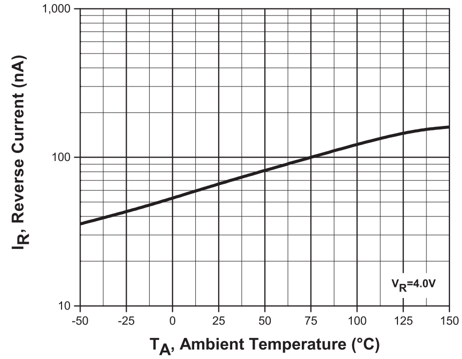
TLM2D3D6 (REV: R2)

LEAD CODE:
1) Cathode
2) Anode

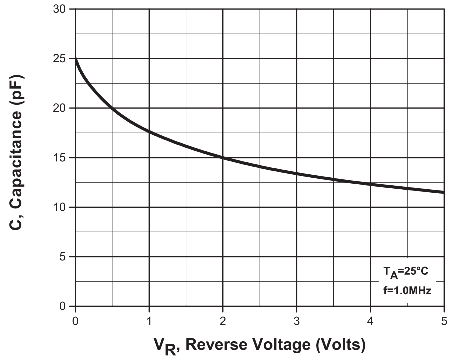
MARKING CODE: S

TYPICAL ELECTRICAL CHARACTERISTICS

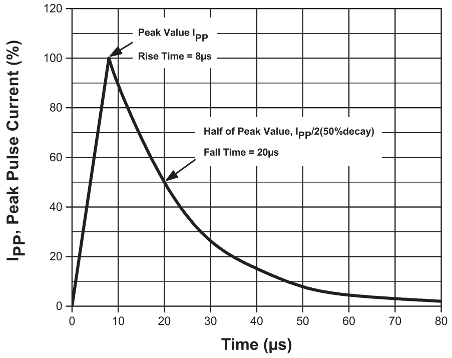
Leakage Current



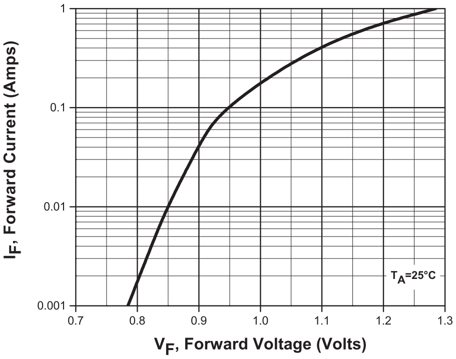
Capacitance



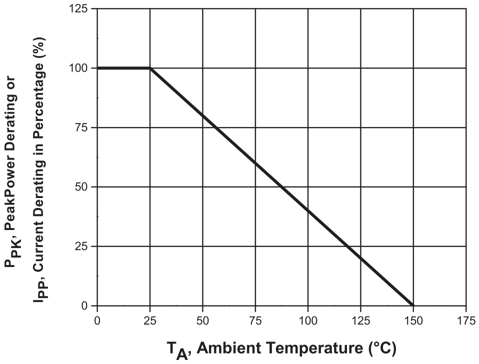
8 x 20 µs Pulse Waveform



Forward Voltage



Power & Current Derating



R1 (23-January 2013)